

Unlock New Possibilities in Si&SiC with Proton&Helium Implantation

From lifetime control to isolation layers – tailored solutions for your devices

APPLICATIONS



SF-KHII®

Suppress stacking fault expansion



Lifetime Control

Optimize carrier lifetime for power devices



Isolation Layers

Create precise buried insulating regions



WHY CHOOSE OUR SERVICE?

Optimize Material Performance:

Elevating Si & SiC Performance through Ion Implantation

R&D Testing Made Easy:

Easily Start Testing with Our Equipment & Systems

Flexible Scalability:

From Prototype to Mass Production – We Provide the Solution



SHI-ATEX

E-mail



Ion Implantation into Semiconductor

Get To Know Us

1

Contract processing service!

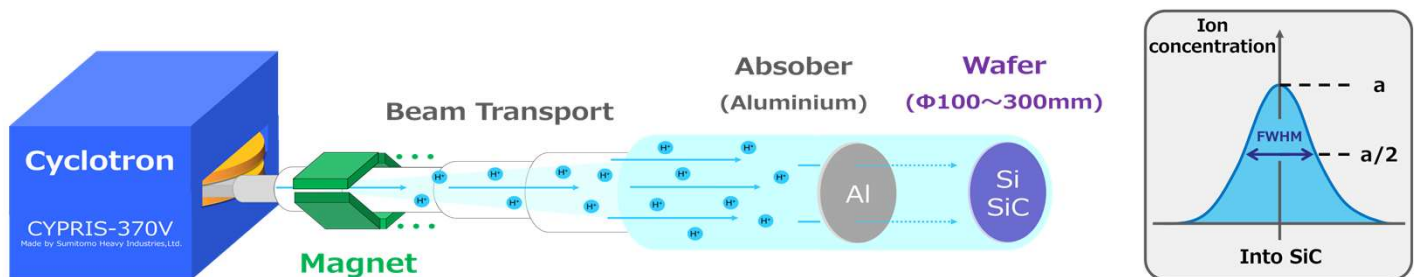
2

Implanting proton and helium ions!

3

High-energy light ion implantation!

Implanter Spec.



	Gas	Ion	Energy	Into SiC (μm)	FWHM (μm)
Cyclotron Spec.	Hydrogen	H^+	2MeV	0~29	1
		H^+	4MeV	0~113	4
		H^+	8MeV	0~320	11
	Helium-3	$^3\text{He}^{2+}$	23MeV	0~229	4
	Helium-4	$^4\text{He}^{2+}$	17MeV	0~114	2
Tandem Spec.	Hydrogen	H^+	0.26~2.40MeV	1.6~43.0	~1.7

